



Status of CBM-GAS-XYTER

Latest Results of the Self-Triggered Digitizer Chip



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1. Introduction

Requirements/Motivation

- Application:
 - Main task: gas chamber readout for CBM TRD
 - Application in other FAIR detectors also conceivable
- We need a <u>self-triggered</u> readout chip that has:
 - 32-64 mixed-signal channels
 - Low noise & power charge amplification (order of 1000e ENC @ 30pF det.)
 - Bandwidth limitation (2nd order shaper or higher, about 90ns shaping time)
 - Digitization (7-10 bit @ 5-30 MHz)
 - Time stamping (necessary time resolution depends on ADC sample speed)
 - In-channel data processing (ion tail cancellation, baseline correction, ...)
 - Inter-channel network (e.g. token ring network)
 - Inter-chip network (pass the data to the next stage)



Conceptual Data Flow Diagram



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Status of Development



Preamp, Shaper, ADC

- Several test-ASICs successfully realized
- First test-chip including an ADC (next to last chip) showed promising results as shown in Split
- <u>Preliminary measurement</u> <u>results of current test-chip</u> <u>will be presented</u>

Hit detector, data generator and token ring

- Design of data flow and control concept completed
- 1st iteration of Verilog description finished
- First simulation results will be presented

Infinite Impulse Response Filter (IIR)

- Theoretically well understood, abstract
 Mathematica calculations completed
- Simplified Verilog description has been written
- <u>First simulation results will be presented</u>

2. Current Test-Chip Architecture

Block Diagram of Current ASIC





Current Test-Chip: Layout



Bias circuitry (12 current DACs) 26 preamp/shaper channels Detector capacitors (5pF per block) 8 pipelined ADCs ADC control + bias 5.2 kBit shift register matrix Control + readout/decoder logic blocks Test circuits



Reminder: Preamplifier/Shaper Circuit



$$H(s) \approx \frac{A_{DC}}{(1+sR_{S}C_{S})^{2}}$$

- O'Connor FB
- 2nd order shaper
- Shaping time: 82 ns
- Unified amplifier cell
- N-MOS input
- ≈ 3.6 mW/channel

New:

- Scaled lengths of input NMOS (180, 250, 320, 390, 460nm)
- Re-Layout of input NMOS: The (long) gate-fingers have been cut into smaller pieces to decrease gate resistance

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Reminder: Algorithmic ADC Design

- 8 (scaled) pipeline stages, therefore 9 Bit design
- Algorithmic working principle ("1.5 redundant Bits" / conversion step)
- 25 MSamples/s, layout only 130x120 μ m², power consumption 4.5 mW
- Core unit: Novel current storage cell:





3. Measurement Results

Test Setup





Shaper Pulse



Noise Results



Characteristic ADC Curve



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Digitized Pulses





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4. Digital Development

IIR Filter (Ion Tail Cancellation) Diagram



Mathematica: IIR Filter (Ion Tail Cancellation)



Digital Simulation: IIR Filter (Ion Tail Cancellation)



- **RED**: IIR filter input pulse with very long ion tail
- BLUE: IIR output after ion tail cancellation (preliminary results)
 - strong overcompensation, but probably due to quantization (compare to Mathematica results)
 - adjustment of filter factors should lead to better results

Digital Hit Detector and Package Builder



Example 1: Internal Hit



Example 2: External Hit



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Example 3: Internal Double Hit



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5. Excursion to UMC 90nm

CSA Submission in UMC 90nm

Motivation

- UMC 90nm technology available via Europractice
- Still a lot of free space on our first 90nm multi-design test-chip (VCO, SRAM, CMOScounter, ...)
- Large deviation between measured and simulated noise in 180nm
- General discussion in analog design: 180nm vs. 90nm
- => Submission of a simple CSA design (preamp, shaper, discriminator) on March 22, 2010





90nm CSA Characteristics



Characteristics from simulation

- 3 channels with on-die detector capacitors (0pF, 12.6pF, 25.2pF)
- NMOS input, O'Connor feedback, 2nd order shaper
- Peaking-Time: 83ns, Rise-Time: 47ns
- Power consumption: 2.3mW (VDD 1.0V)
- Noise: 377e @ 20pF
- Note: no optimization, minimum on-chip bias circuitry, 5 days of work for the whole design

90nm CSA Shaper Output Pulse





6. Future Plans and Summary

Floor Plan Proposal



- 3 x 2 mm² estimated die size
- 32 channels, 40-80 μ m pitch, (mostly) symmetric layout, low(er) IR-drops
- Detector connection-pads on two sides (chips will probably be attached to back of detectormodule, this relaxes routing/spacing)



Summary

Status of analog chip design:

- Measurement results so far promising
- Further tests still have to be done (find optimal settings, test ESD pads, connect CSAs to ADCs, ...)

Status of digital channel back-end design:

- First design proposal of digital back-end completed
- Good simulation results, ongoing development of larger verification environment
- Large construction site: IIR filter (good topic for a diploma thesis)

Next Steps:

- Complete chip measurement
- Connect chip to some gas-chamber (e.g. from Frankfurt)
- Start tests of digital channel back-end on some FPGA board
- Maybe submit a completely digital test-ASIC
- Do first steps towards the CBM-GAS-XYTER design (layout concept, ...)
- Find a better name for CBM-GAS-XYTER



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Thank you!



Raw Data vs. Extracted Data: System Options



level of integration

Chip: Preamp/Shaper Results

- measured. normal measured. long 1400 Noise was measured. no triwell measured. old measured with ssimulated. normal simulated. long 1200 curve scans using simulated, no triwell simulated old the discriminator 1000 Injection capacitor calibrated via test Voise [ENC] 800 circuit 4 different 600 preamplifier types: old, 400 normal, no triwell, long 200 0 5 10 15 35 0 20 25 30 40 Detector capacitance [pF]
- Results:
 - Noise values of normal (triwell NMOS input, minimal length) and no triwell (NMOS without triwell, minimal length) channel show <u>no significant difference compared to the</u> <u>old channel</u> => values still much worse than simulated
 - Noise slope of long (triwell NMOS input, 320 nm length) channel about <u>two-times</u> <u>smaller</u> => about 800 e ENC @ 30 pF achievable, still worse than in simulation

Chip: ADC Results



